

R-C Thermal Model Parameters

DESCRIPTION

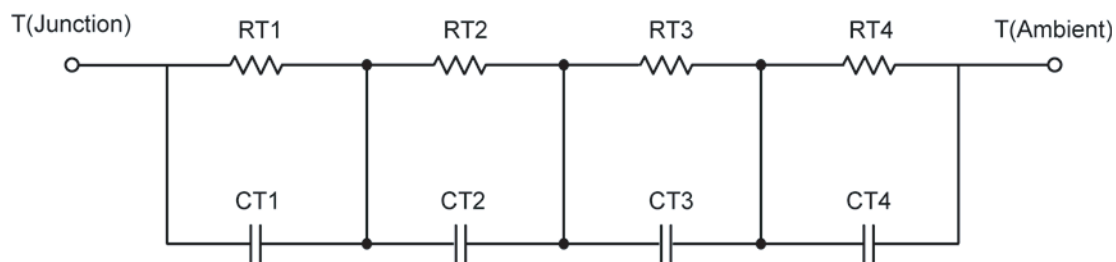
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

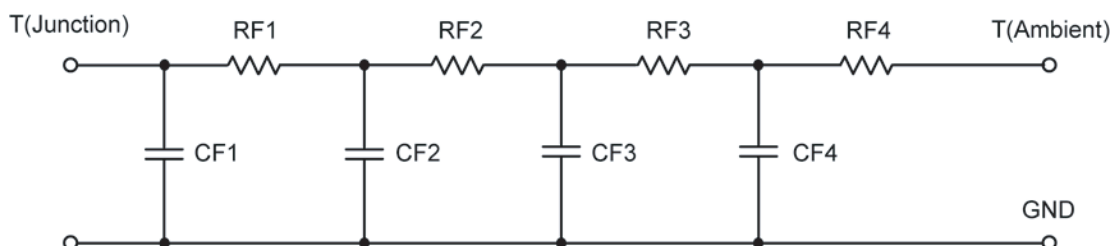
For a detailed explanation of implementing these values in P-Spice, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-Spice Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	21.8201	N/A	11.3853
RT2	8.1139	N/A	4.0448
RT3	32.3427	N/A	13.1289
RT4	47.1462	N/A	8.4704
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	10.8053 m	N/A	4.6399 m
CT2	804.8542 u	N/A	413.3234 u
CT3	57.2589 m	N/A	30.2199 m
CT4	1.4498	N/A	217.5051 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	7.5110	N/A	5.6037
RF2	25.8169	N/A	14.8167
RF3	31.4783	N/A	13.4714
RF4	44.2066	N/A	3.1907
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	525.2266 μ	N/A	426.5868 μ
CF2	6.7261 m	N/A	4.2031 m
CF3	45.5528 m	N/A	38.5086 m
CF4	1.4272	N/A	625.8011 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

